



SANYO Semiconductors

DATA SHEET

MCH5837

MOSFET : N-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

General-Purpose Switching Device Applications

Features

- Composite type with an N-channel silicon MOSFET and a schottky barrier diode (SS10015M) contained in one package facilitating high-density mounting.
- [MOSFET]
 - Low ON-resistance.
 - 1.8V drive.
- [SBD]
 - Short reverse recovery time.
 - Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		2	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	8	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : YB

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SANYO Semiconductor Co., Ltd.

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Parameter	Symbol	Conditions	Ratings	Unit
[SBD]				
Repetitive Peak Reverse Voltage	VRRM		15	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		15	V
Average Output Current	IO		1	A
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	3	A
Junction Temperature	TJ		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

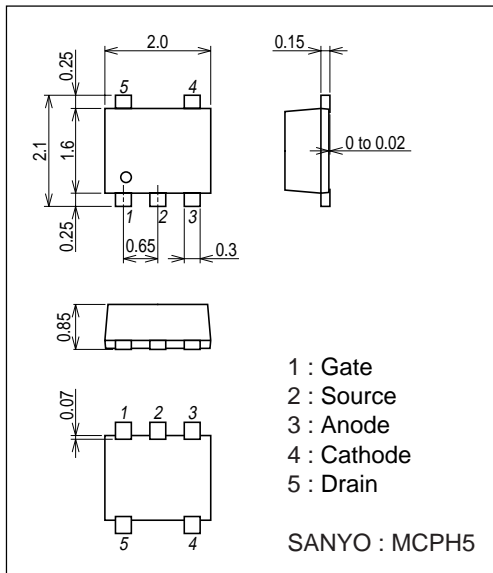
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=20V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=1A	1.4	2.4		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1A, VGS=4V		110	145	mΩ
	RDS(on)2	ID=0.5A, VGS=2.5V		150	215	mΩ
	RDS(on)3	ID=0.1A, VGS=1.8V		210	320	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		115		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		35		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		25		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		7.5		ns
Rise Time	tr	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		20		ns
Fall Time	tf	See specified Test Circuit.		30		ns
Total Gate Charge	Qg	VDS=10V, VGS=4V, ID=2A		1.8		nC
Gate-to-Source Charge	Qgs	VDS=10V, VGS=4V, ID=2A		0.35		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=10V, VGS=4V, ID=2A		0.5		nC
Diode Forward Voltage	VSD	IS=2A, VGS=0V		0.86	1.2	V
[SBD]						
Reverse Voltage	VR	IR=0.5mA	15			V
Forward Voltage	VF1	IF=0.3A		0.3	0.33	V
	VF2	IF=0.5A		0.33	0.36	V
Reverse Current	IR	VR=6V			90	μA
Interterminal Capacitance	C	VR=10V, f=1MHz		20		pF
Reverse Recovery Time	trr	IF=IR=100mA, See specified Test Circuit.			10	ns

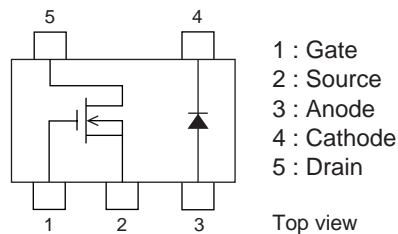
Package Dimensions

unit : mm (typ)

7021A-008



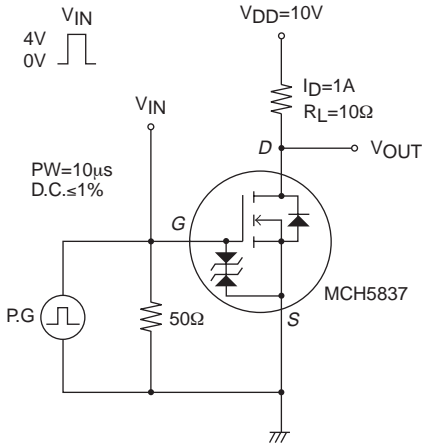
Electrical Connection



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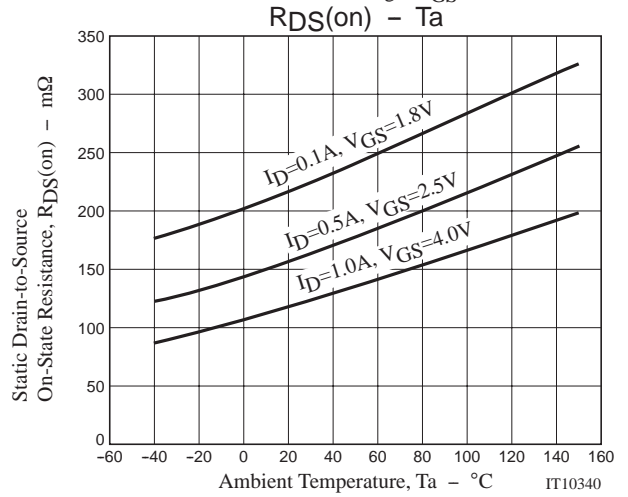
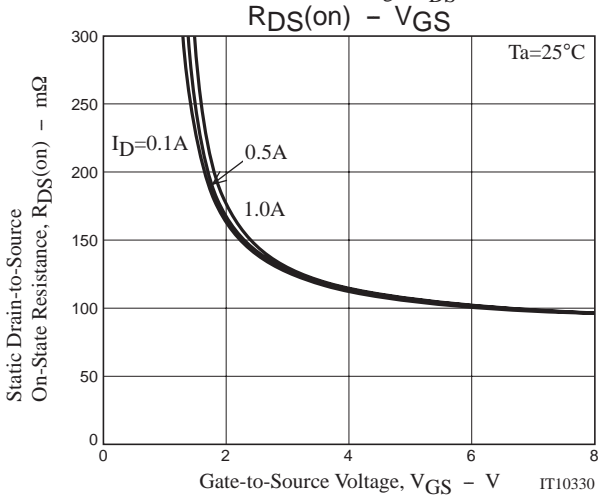
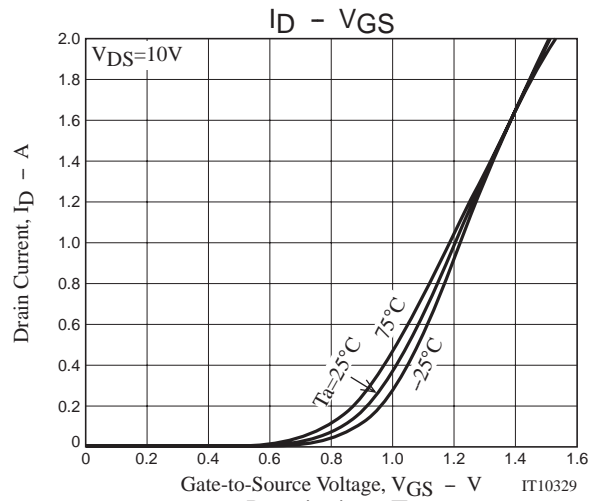
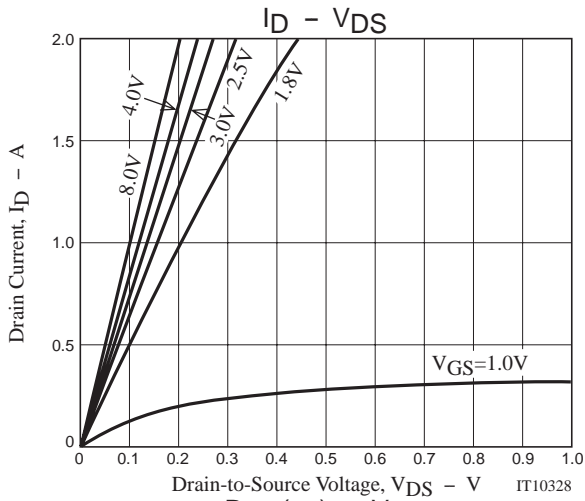
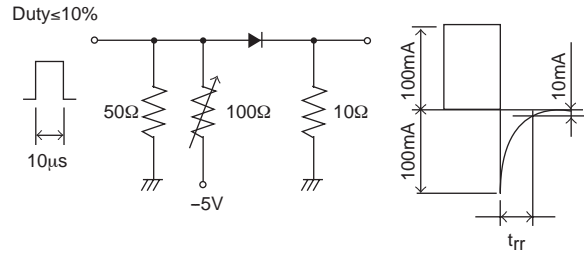
Switching Time Test Circuit

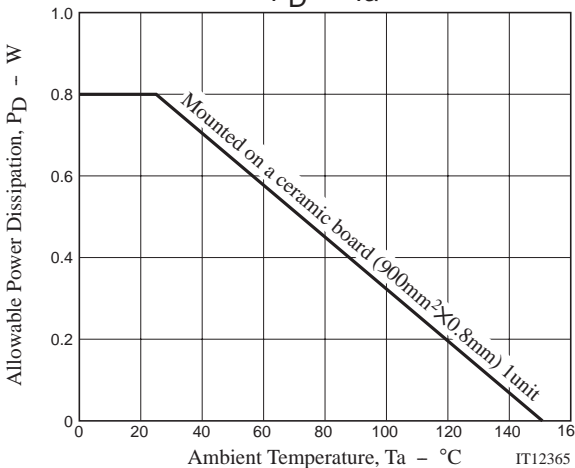
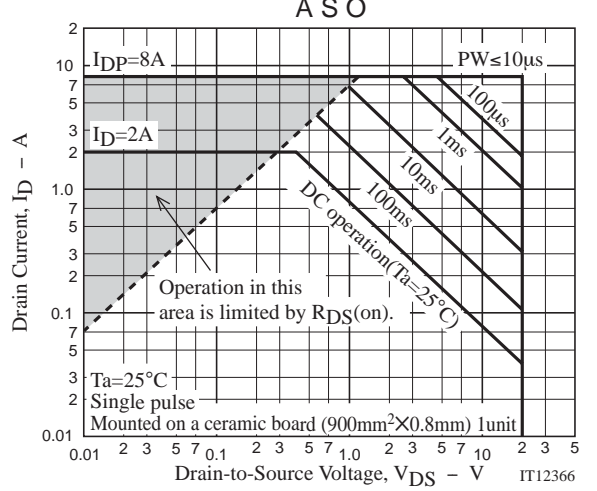
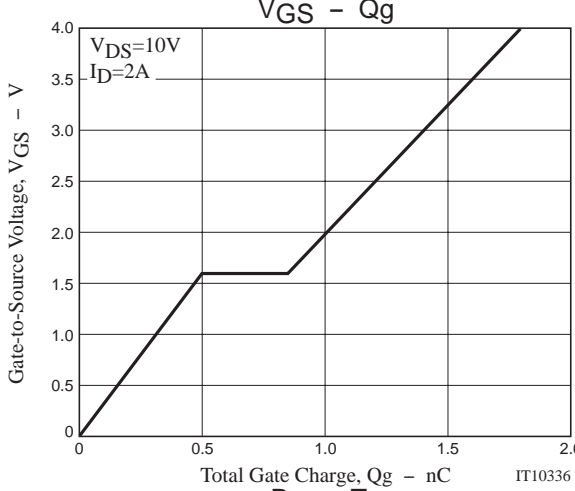
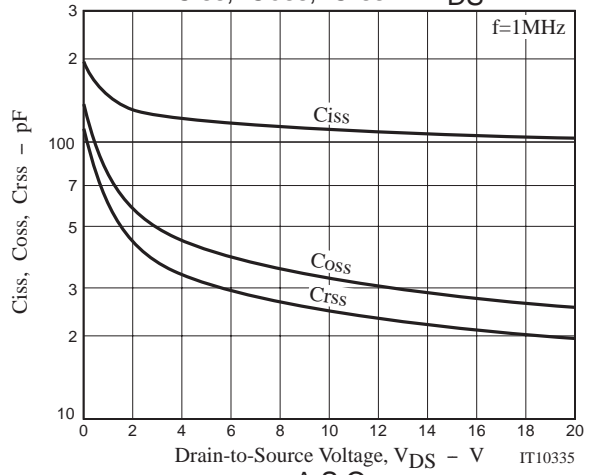
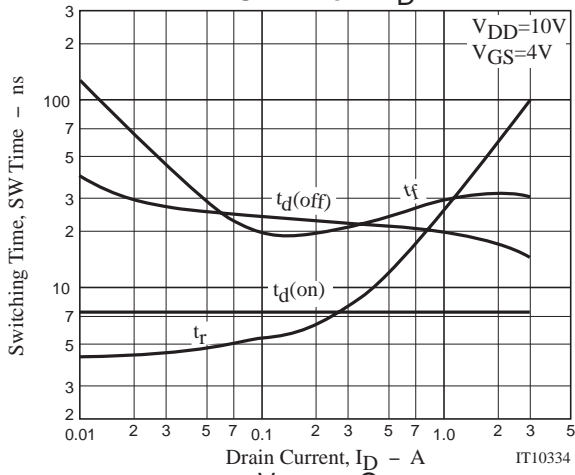
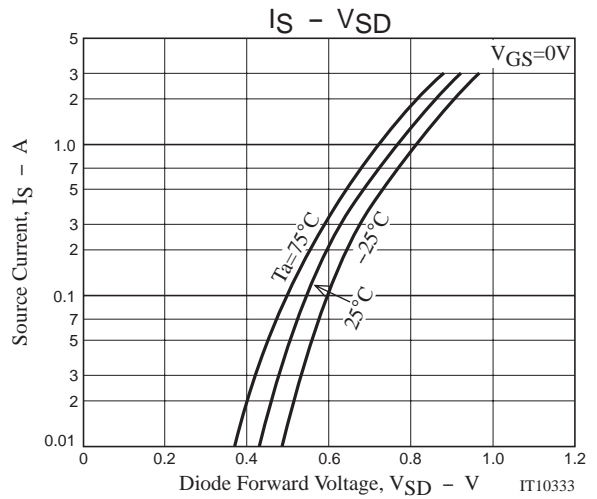
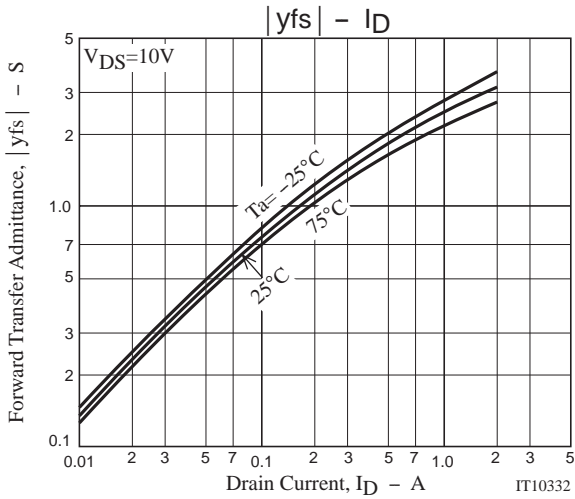
[MOSFET]



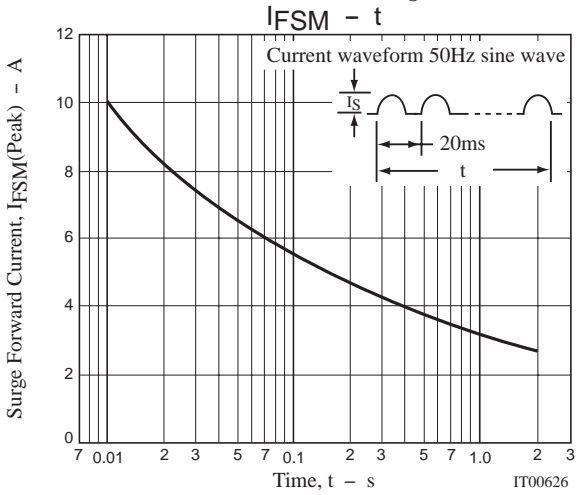
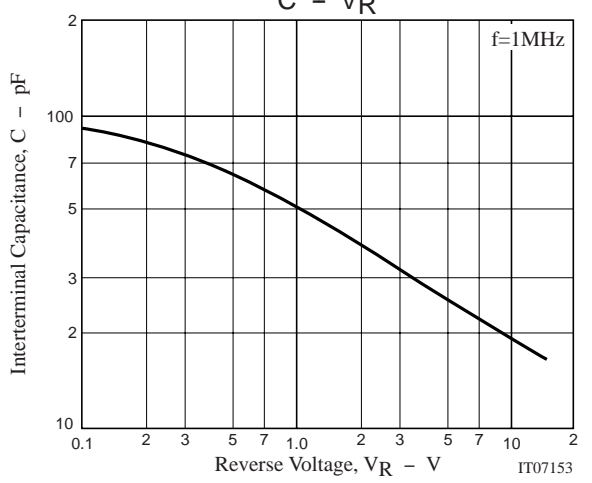
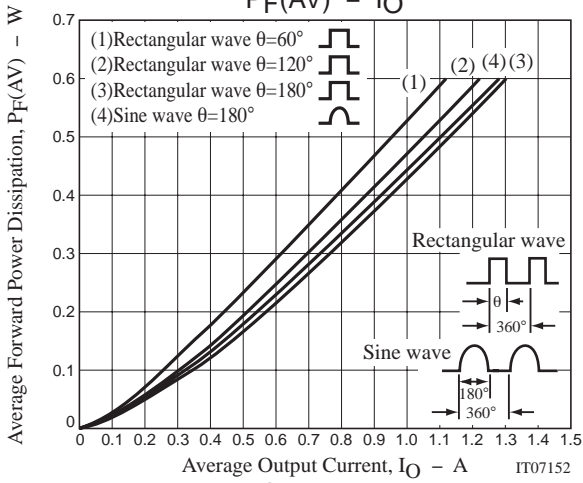
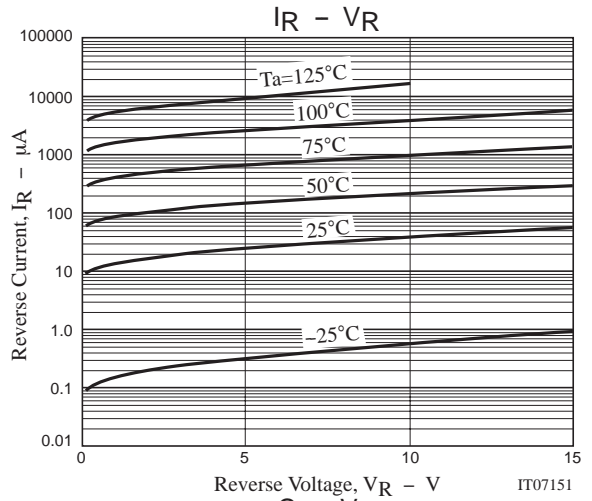
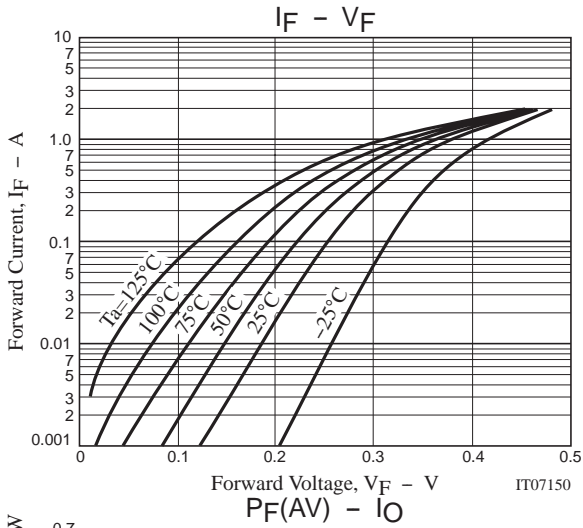
t_{rr} Test Circuit

[SBD]





MCH5837



Note on usage : Since the MCH5837 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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